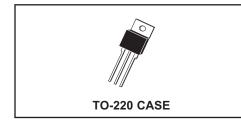


COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS



## cent Semiconductor Corp.

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# **DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N6040 and 2N6043 Series types are Complementary Silicon Power Transistors, manufactured by the epitaxial base process, designed for general purpose amplifier applications.

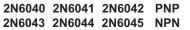
### MARKING: FULL PART NUMBER

|                                   | 2N6040  | 2N6041  | 2N6042  |   |
|-----------------------------------|---|---|---|---|
| SYMBOL                            | <u>2N6043</u>   | <u>2N6044</u>   | <u>2N6045</u>   | UNITS   |
| V <sub>CBO</sub>                  | 60  | 80  | 100   | V   |
| VCEO                              | 60  | 80  | 100   | V   |
| V <sub>EBO</sub>                  |   | 5.0   |   | V   |
| ۱ <sub>C</sub>                    |   | 8.0   |   | А   |
| ICM                               |   | 16  |   | А   |
| ۱ <sub>B</sub>                    |   | 120   |   | mA  |
| PD                                |   | 75  |   | W   |
| T <sub>J</sub> , T <sub>sta</sub> |   | -65 to +150   |   | °C  |
| ΘJC                               |   | 1.67  |   | °C/W  |
|                                   | VCBO<br>VCEO<br>VEBO<br>IC<br>ICM<br>IB<br>PD<br>TJ, Tstg | SYMBOL 2N6043   V <sub>CBO</sub> 60   V <sub>CEO</sub> 60   V <sub>EBO</sub> 1   I <sub>C</sub> I   I <sub>B</sub> P <sub>D</sub> T <sub>J</sub> , T <sub>stg</sub> T | SYMBOL 2N6043 2N6044   VCBO 60 80   VCEO 60 80   VEBO 5.0 Ic   IC 8.0 Ic   IB 120 PD   FJ, Tstg -65 to +150 | SYMBOL 2N6043 2N6044 2N6045   V <sub>CBO</sub> 60 80 100   V <sub>CEO</sub> 60 80 100   V <sub>CEO</sub> 60 80 100   V <sub>CEO</sub> 60 80 100   V <sub>EBO</sub> 5.0 100   I <sub>C</sub> 8.0 100   I <sub>C</sub> 16 18   I <sub>B</sub> 120 P <sub>D</sub> P <sub>D</sub> 75 75   T <sub>J</sub> , T <sub>stg</sub> -65 to +150 |

#### **ELECTRICAL CHARACTERISTICS:** ( $T_C$ =25°C unless otherwise noted)

| SYMBOL               | TEST CONDITIONS   | MIN   | MAX    | UNITS |
|----------------------|---|-------|--------|-------|
| ICBO                 | V <sub>CB</sub> =Rated V <sub>CBO</sub>   |       | 20     | μA    |
| ICEV                 | V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>BE(OFF)</sub> =1.5V                        |       | 20     | μA    |
| ICEV                 | V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>BE(OFF)</sub> =1.5V, T <sub>C</sub> =150°C |       |        | μA    |
| ICEO                 | V <sub>CE</sub> =Rated V <sub>CEO</sub>   |       | 20     | μA    |
| I <sub>EBO</sub>     | V <sub>EB</sub> =5.0V   |       | 2.0    | mA    |
| BVCEO                | I <sub>C</sub> =100mA (2N6040, 2N6043)  | 60    |        | V     |
| BVCEO                | I <sub>C</sub> =100mA (2N6041, 2N6044)  | 80    |        | V     |
| BVCEO                | I <sub>C</sub> =100mA (2N6042, 2N6045)  | 100   |        | V     |
| V <sub>CE(SAT)</sub> | I <sub>C</sub> =4.0A, I <sub>B</sub> =16mA (2N6040, 2N6041, 2N6043, 2N6044)                 |       |        | V     |
| V <sub>CE(SAT)</sub> | I <sub>C</sub> =3.0A, I <sub>B</sub> =12mA (2N6042, 2N6045)                                 |       | 2.0    | V     |
| V <sub>CE(SAT)</sub> | I <sub>C</sub> =8.0A, I <sub>B</sub> =80mA  |       | 4.0    | V     |
| V <sub>BE(SAT)</sub> | I <sub>C</sub> =8.0A, I <sub>B</sub> =80mA  |       | 4.5    | V     |
| V <sub>BE(ON)</sub>  | V <sub>CE</sub> =4.0V, I <sub>C</sub> =4.0A   |       | 2.8    | V     |
| h <sub>FE</sub>      | V <sub>CE</sub> =4.0V, I <sub>C</sub> =4.0A (2N6040, 2N6041, 2N6043, 2N6044)                | 1,000 | 20,000 |       |
| h <sub>FE</sub>      | V <sub>CE</sub> =4.0V, I <sub>C</sub> =3.0A (2N6042, 2N6045)                                | 1,000 | 20,000 |       |
| h <sub>FE</sub>      | V <sub>CE</sub> =4.0V, I <sub>C</sub> =8.0A   | 100   |        |       |
|                      |   |       |        |       |

R1 (16-November 2009)

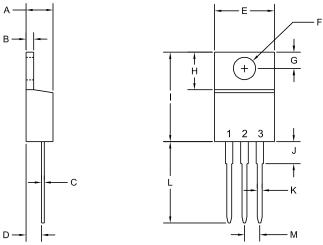




### COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

| ELECTRICAL CHARACTERISTICS - Continued: (T <sub>C</sub> =25°C unless otherwise noted) |   |     |     |       |  |
|---|---|-----|-----|-------|--|
| SYMBOL  | TEST CONDITIONS   | MIN | MAX | UNITS |  |
| h <sub>fe</sub>   | V <sub>CE</sub> =4.0V, I <sub>C</sub> =3.0A, f=1.0kHz         | 300 |     |       |  |
| f <sub>T</sub>  | V <sub>CE</sub> =4.0V, I <sub>C</sub> =3.0A, f=1.0MHz         | 4.0 |     | MHz   |  |
| Cob   | V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=100kHz (NPN Types) |     | 200 | pF    |  |
| Cob   | $V_{CB}$ =10V, I <sub>E</sub> =0, f=100kHz (PNP Types)        |     | 300 | pF    |  |

### **TO-220 CASE - MECHANICAL OUTLINE**



R2

| DIMENSIONS       |        |       |        |               |  |
|------------------|--------|-------|--------|---------------|--|
|                  | INCHES |       | MILLIM | <b>IETERS</b> |  |
| SYMBOL           | MIN    | MAX   | MIN    | MAX           |  |
| А                | 0.170  | 0.190 | 4.31   | 4.82          |  |
| В                | 0.045  | 0.055 | 1.15   | 1.39          |  |
| С                | 0.013  | 0.026 | 0.33   | 0.65          |  |
| D                | 0.083  | 0.107 | 2.10   | 2.72          |  |
| Е                | 0.394  | 0.417 | 10.01  | 10.60         |  |
| F (DIA)          | 0.140  | 0.157 | 3.55   | 4.00          |  |
| G                | 0.100  | 0.118 | 2.54   | 3.00          |  |
| Н                | 0.230  | 0.270 | 5.85   | 6.85          |  |
|                  | 0.560  | 0.625 | 14.23  | 15.87         |  |
| J                | -      | 0.250 | -      | 6.35          |  |
| K                | 0.025  | 0.038 | 0.64   | 0.96          |  |
| L                | 0.500  | 0.579 | 12.70  | 14.70         |  |
| М                | 0.090  | 0.110 | 2.29   | 2.79          |  |
| TO-220 (REV: R2) |        |       |        |               |  |

1) BASE

2) COLLECTOR

3) EMITTER

4) COLLECTOR

MARKING: FULL PART NUMBER

R1 (16-November 2009)

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- Inventory bonding
- Consolidated shipping options

- Custom bar coding for shipments
- Custom product packing

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Central's applications engineering team is ready to discuss your design challenges. Just ask.

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- SPICE models
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- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

### CONTACT US

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